



MJE13005

SILICON POWER TRANSISTORS

NPN power transistors in a TO-220 package. They are intended for high voltage, high speed power switching inductive circuits where fall time is critical. They are particularly suited for 115V and 220V SWITCHMODE applications such as switching regulator's, inverters, motor controls, solenoid/relay drivers and deflection circuits
Compliance to RoHS.

ABSOLUTE MAXIMUM RATINGS

Symbol	Ratings		Value	Unit
V _{CEO}	Collector-Emitter Voltage		400	V
V _{CBO}	Collector-Base Voltage		700	V
V _{EBO}	Emitter-Base Voltage		9	V
I _C	Collector Current		4	A
I _{CM}	Collector Peak Current (*)		8	A
I _B	Base Current		2	A
I _{BM}	Base Peak Current (*)		4	A
I _E	Emitter Current		6	A
I _{EM}	Emitter Peak Current (*)		12	A
P _T	Power Dissipation at Case Temperature	@ T _{mb} < 25°	75	W
	Power Dissipation at free Air Temperature		2	
t _J	Junction Temperature		150	°C
t _s	Storage Temperature range		-65 to +150	

(*)Pulse Width = 5ms, duty cycle <10%.

THERMAL CHARACTERISTICS

Symbol	Ratings	Value	Unit
R_{thJC}	From Junction to Case Thermal Resistance	1.67	$^\circ\text{C/W}$
R_{thJA}	From Junction to Free-Air Thermal Resistance	62.5	

MJE13005

ELECTRICAL CHARACTERISTICS

TC=25°C unless otherwise noted

Symbol	Ratings	Test Condition(s)	Min	Typ	Max	Unit
V_{CEO}	Collector-Emitter Sustaining Voltage (*)	$I_C = 10 \text{ mA}, I_B = 0$	400	-	-	V
I_{CBO}	Collector- Cutoff Current	$V_{CB} = 700 \text{ V}$ $I_B = 0$	$T_C = 25^\circ\text{C}$ $T_C = 100^\circ\text{C}$	- -	1 5	mA
I_{EBO}	Emitter Cutoff Current	$V_{EB} = 9 \text{ V}, I_C = 0$	-	-	1	mA
$V_{CE(SAT)}$	Collector-Emitter saturation Voltage (*)	$I_C = 1 \text{ A}, I_B = 200 \text{ mA}$ $I_C = 2 \text{ A}$ $I_B = 500 \text{ mA}$ $I_C = 4 \text{ A}, I_B = 1 \text{ A}$	$T_C = 25^\circ\text{C}$ $T_C = 100^\circ\text{C}$	- - - -	0.5 0.6 1 1	V
$V_{BE(SAT)}$	Base-Emitter Saturation Voltage (*)	$I_C = 1 \text{ A}, I_B = 200 \text{ mA}$ $I_C = 2 \text{ A}$ $I_B = 500 \text{ mA}$	$T_C = 25^\circ\text{C}$ $T_C = 100^\circ\text{C}$	- - -	1.2 1.6 1.5	V
h_{FE}	Forward Current transfer ratio (*)	$V_{CE} = 5.0 \text{ V}, I_C = 1 \text{ A}$ $V_{CE} = 5.0 \text{ V}, I_C = 2 \text{ A}$	10 8	- -	60 40	-
f_T	Transition Frequency	$V_{CE} = 10 \text{ V}, I_C = 0.5 \text{ A}, f = 1 \text{ MHz}$	4	-	-	MHz
C_{OB}	Output Capacitance	$I_E = 0; V_{CB} = 10 \text{ V}; f = 1 \text{ MHz}$	-	65	-	pF

(*) Pulse Width $\approx 300 \mu\text{s}$, Duty Cycle $\angle 2.0\%$

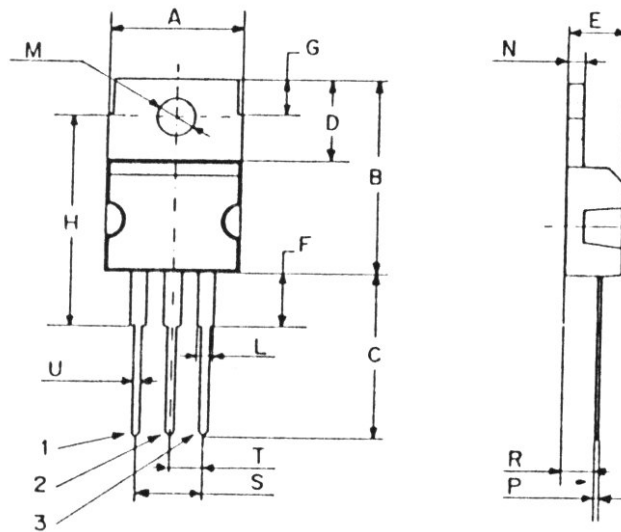
SWITCHING TIMES.

Symbol	Ratings	Test Condition(s)	Min	Typ	Max	Unit
t_d	Delay Time	$V_{CC} = 125 \text{ V}; I_C = 2 \text{ A}$ $I_{B1} = -I_{B2} = 400 \text{ mA}$ $t_p = 25 \mu\text{s}$, duty cycle $< 1\%$.	-	-	0.1	μs
t_r	Rise time		-	-	0.7	
t_s	Storage Time		-	-	4	
t_f	Fall Time		-	-	0.9	

MJE13005

MECHANICAL DATA CASE TO-220

DIMENSIONS (mm)		
	Min.	Max.
A	9,90	10,30
B	15,65	15,90
C	13,20	13,40
D	6,45	6,65
E	4,30	4,50
F	2,70	3,15
G	2,60	3,00
H	15,75	17,15
L	1,15	1,40
M	3,50	3,70
N	-	1,37
P	0,46	0,55
R	2,50	2,70
S	4,98	5,08
T	2,49	2,54
U	0,70	0,90



Pin 1 :	Base
Pin 2 :	Collector
Pin 3 :	Emitter
Case :	Collector

Revised September 2012

Information furnished is believed to be accurate and reliable. However, Comset Semiconductors assumes no responsibility for the consequences of use of such information nor for any infringement of patents or other rights of third parties which may results from its use. Data are subject to change without notice. Comset Semiconductors makes no warranty, representation or guarantee regarding the suitability of its products for any particular purpose, nor does Comset Semiconductors assume any liability arising out of the application or use of any product and specifically disclaims any and all liability, including without limitation consequential or incidental damages. Comset Semiconductors' products are not authorized for use as critical components in life support devices or systems.